

## PHASE CONTROL THYRISTORS

■ Junction Size:	Square 110 mils
■ Wafer Size:	4"
■ $V_{RRM}$ Class:	1200 V
■ Passivation Process:	Glassivated MESA
■ Reference IR Packaged Part:	16TTS Series

### Major Ratings and Characteristics

Parameters	Units	Test Conditions
$V_{TM}$ Maximum On-state Voltage	1.4 V	$T_J = 25^\circ\text{C}$ , $I_T = 10\text{ A}$
$V_{RRM}$ Reverse Breakdown Voltage	1200 V	$T_J = 25^\circ\text{C}$ , $I_{RRM} = 100\ \mu\text{A}$ (1)
$I_{GT}$ Max. Required DC Gate Current to Trigger	60 mA	$T_J = 25^\circ\text{C}$ , anode supply = 6 V, resistive load
$V_{GT}$ Max. Required DC Gate Voltage to Trigger	2 V	$T_J = 25^\circ\text{C}$ , anode supply = 6 V, resistive load
$I_H$ Holding Current Range	5 to 100 mA	Anode supply = 6 V, resistive load
$I_L$ Maximum Latching Current	200 mA	Anode supply = 6 V, resistive load

(1) Nitrogen flow on die edge.

### Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 $\mu$ m)
Chip Dimensions	110 x 110 mils (see drawing)
Wafer Diameter	100 mm, with std. <110> flat
Wafer Thickness	350 $\mu$ m $\pm$ 10 $\mu$ m
Maximum Width of Sawing Line	130 $\mu$ m
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

# IR110BG12DCB

Bulletin I0101J 12/01

International  
**IR** Rectifier

## Ordering Information Table

Device Code						
<b>IR</b>	<b>110</b>	<b>B</b>	<b>G</b>	<b>12</b>	<b>D</b>	<b>CB</b>
①	②	③	④	⑤	⑥	⑦

  

<b>1</b>	- International Rectifier Device
<b>2</b>	- Chip Dimension in Mils
<b>3</b>	- Type of Device: B = Wire Bondable SCR
<b>4</b>	- Passivation Process: G = Glassivated MESA
<b>5</b>	- Voltage code: Code x 100 = $V_{RRM}$
<b>6</b>	- Metallization: D = Silver (Anode) - Aluminium (Cathode)
<b>7</b>	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier

## Outline Table

